

TM05N10MI

N-Channel Enhancement Mosfet

General Description

- Low $R_{DS(ON)}$
- RoHS and Halogen-Free Compliant

Applications

- Load switch
- PWM

General Features

$V_{DS} = 100V$ $I_D = 5.0A$

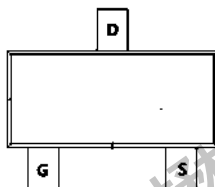
$R_{DS(ON)} = 105(\text{typ.})m\Omega @ V_{GS}=10V$

100% UIS Tested

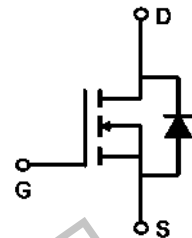
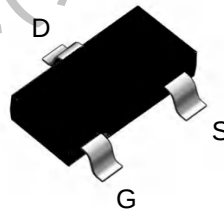
100% R_g Tested



MI:SOT-23-3L



Marking: 1005



Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	5.0	A
$I_D @ T_A=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	4.4	A
I_{DM}	Pulsed Drain Current ²	26	A
$P_D @ T_A=25^\circ\text{C}$	Total Power Dissipation ³	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	48	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	---	$^\circ\text{C/W}$

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Electrical Characteristics@T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V(BR)DSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	100	107	-	V
IDSS	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V,	-	-	1.0	μA
IGSS	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
VGS(th)	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	2.0	3.0	V
RDS(on)	Static Drain-Source on-Resistance note3	V _{GS} =10V, I _D =10A	-	105	125	mΩ
		V _{GS} =4.5V, I _D =8A	-	---	---	mΩ
Ciss	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	-	610	-	pF
Coss	Output Capacitance		-	40	-	pF
Crss	Reverse Transfer Capacitance		-	25	-	pF
Qg	Total Gate Charge	V _{DS} =30V, I _D =10A, V _{GS} =10V	-	12	-	nC
Qgs	Gate-Source Charge		-	2.2	-	nC
Qgd	Gate-Drain("Miller") Charge		-	2.5	-	nC
td(on)	Turn-on Delay Time	V _{DS} =30V, I _D =5A, R _G =1.8Ω, V _{GS} =10V	-	7	-	ns
t _r	Turn-on Rise Time		-	5	-	ns
td(off)	Turn-off Delay Time		-	16	-	ns
t _f	Turn-off Fall Time		-	6	-	ns
IS	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	-	-	5	A
ISM	Pulsed Source Current ^{2,5}		-	-	40	A
VSD	Diode Forward Voltage ²	V _{GS} =0V, I _S =10A	-	-	1.2	V
trr	Body Diode Reverse Recovery Time	I _F =10A, dI/dt=100A/μs	-	21	-	ns
Qrr	Body Diode Reverse Recovery Charge		-	21	-	nC

Note :

- 1.The data tested by surface mounted on a 1 inch² FR-4 board with 20Z copper.
- 2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%
- 3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=11A
- 4.The power dissipation is limited by 150°C junction temperature
- 5 .The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

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Typical Characteristics

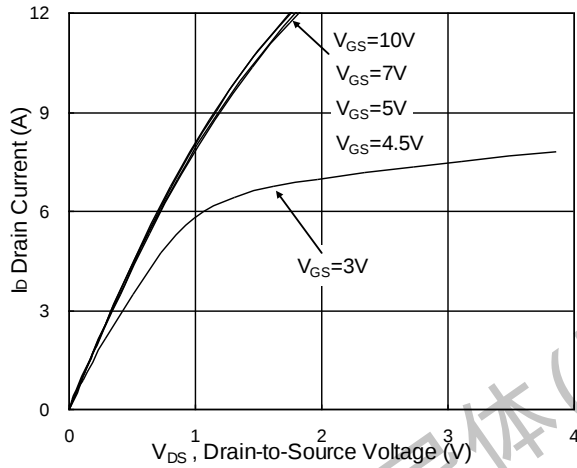


Fig.1 Typical Output Characteristics

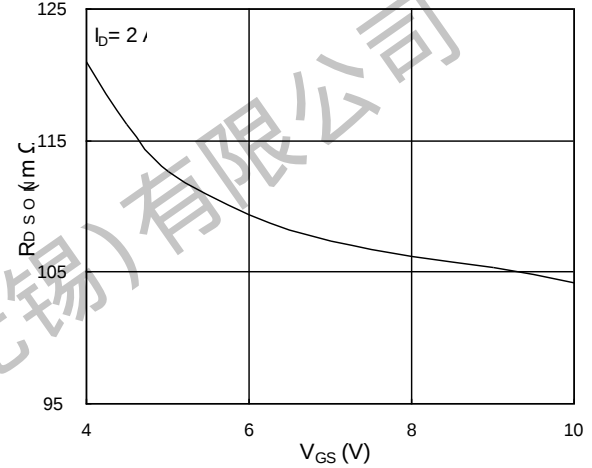


Fig.2 On-Resistance vs. Gate-Source

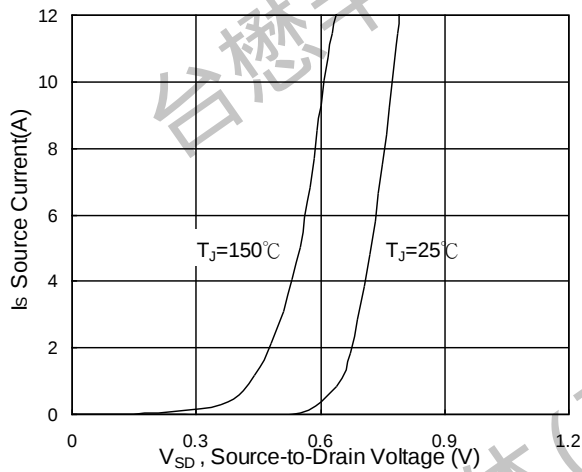


Fig.3 Forward Characteristics Of Reverse

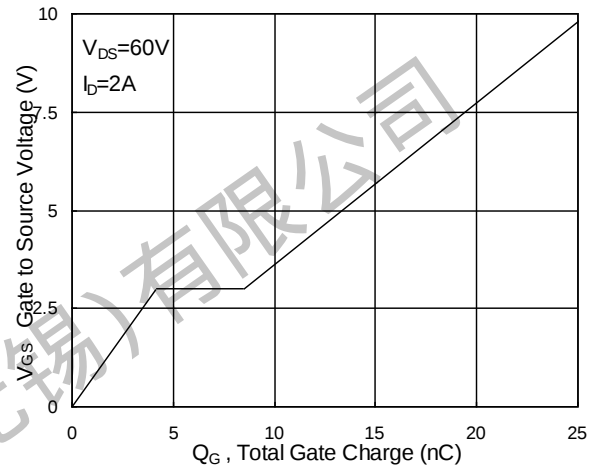


Fig.4 Gate-Charge Characteristics

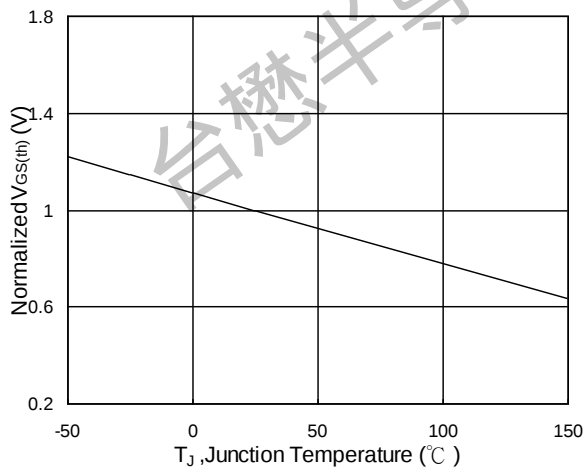


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

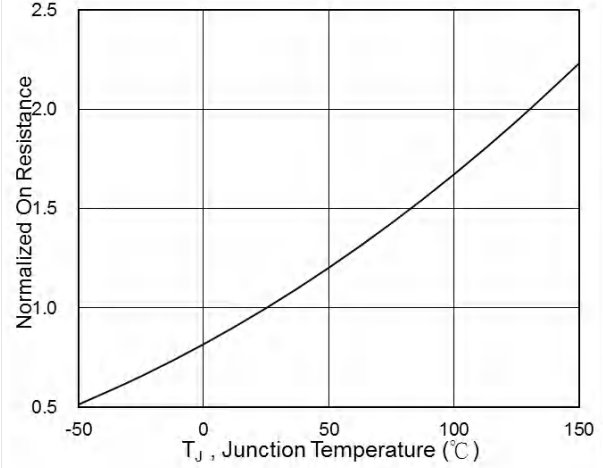


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

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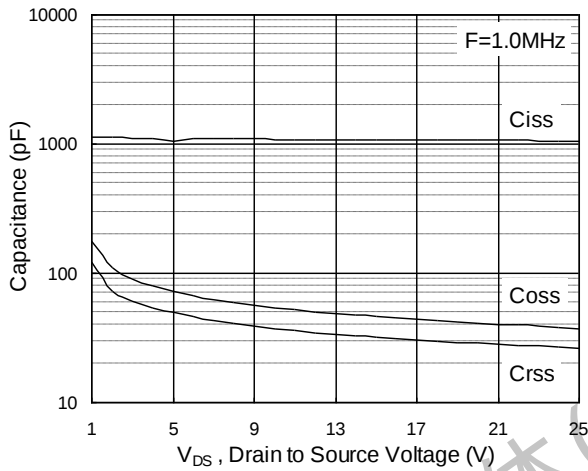


Fig.7 Capacitance

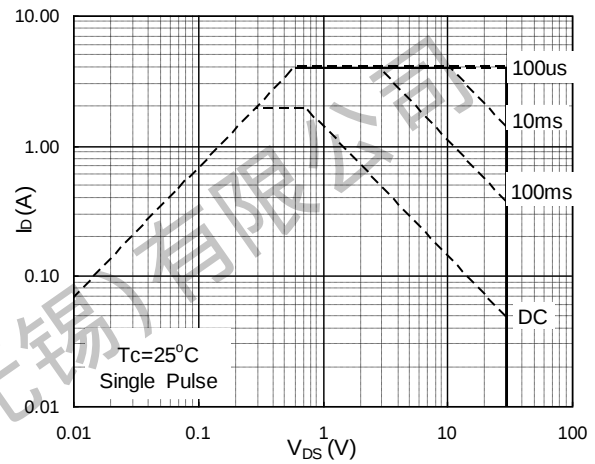


Fig.8 Safe Operating Area

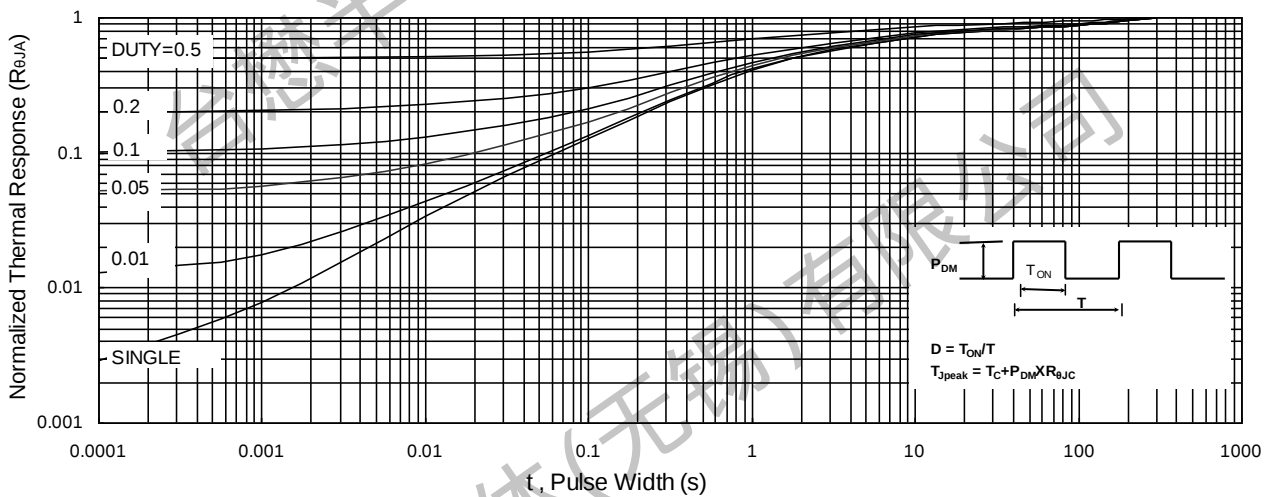


Fig.9 Normalized Maximum Transient Thermal Impedance

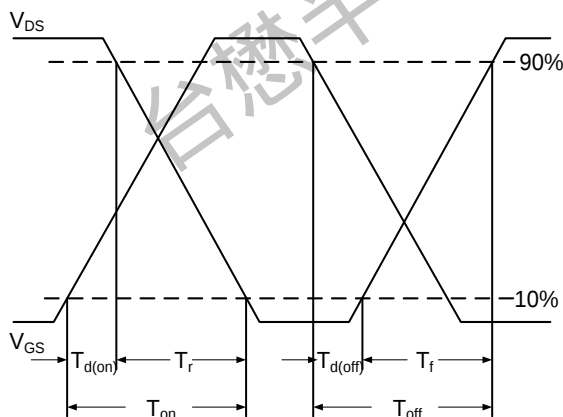


Fig.10 Switching Time Waveform

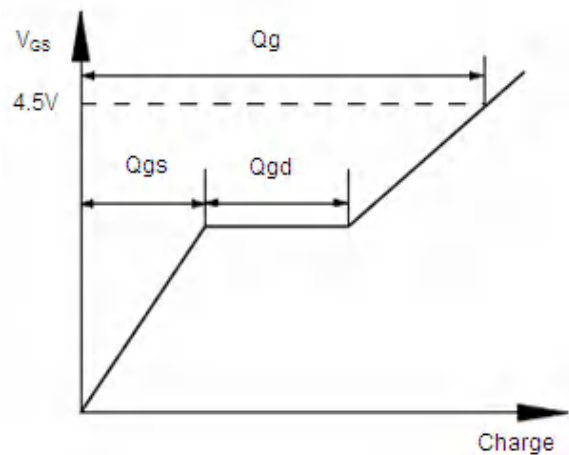
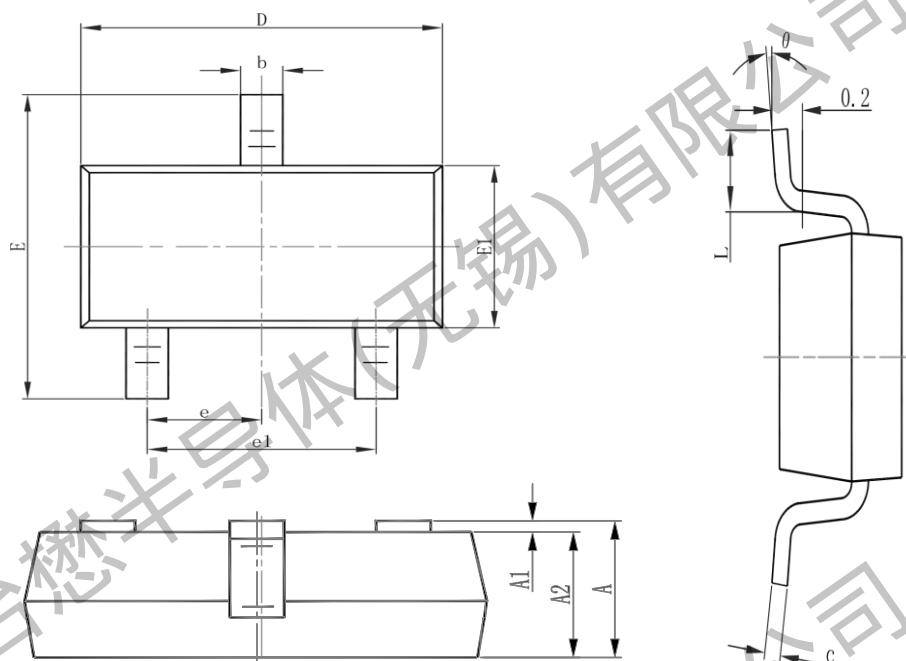


Fig.11 Gate Charge Waveform

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Package Mechanical Data:SOT-23-3L



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

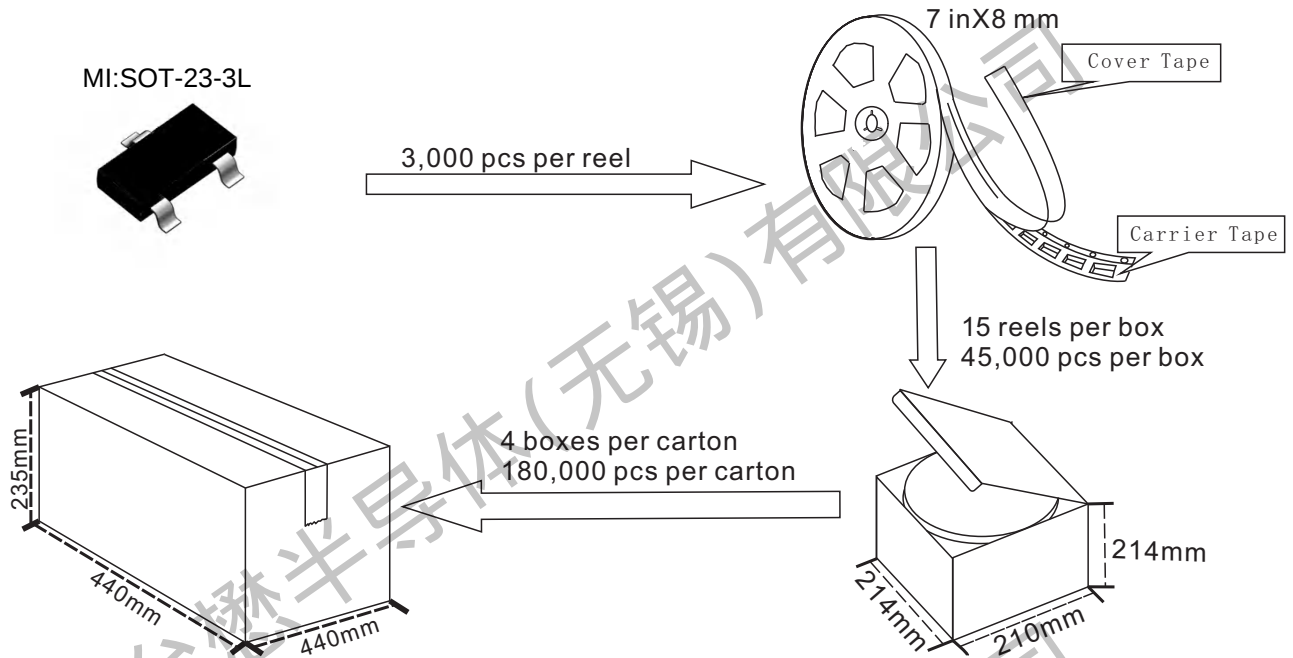


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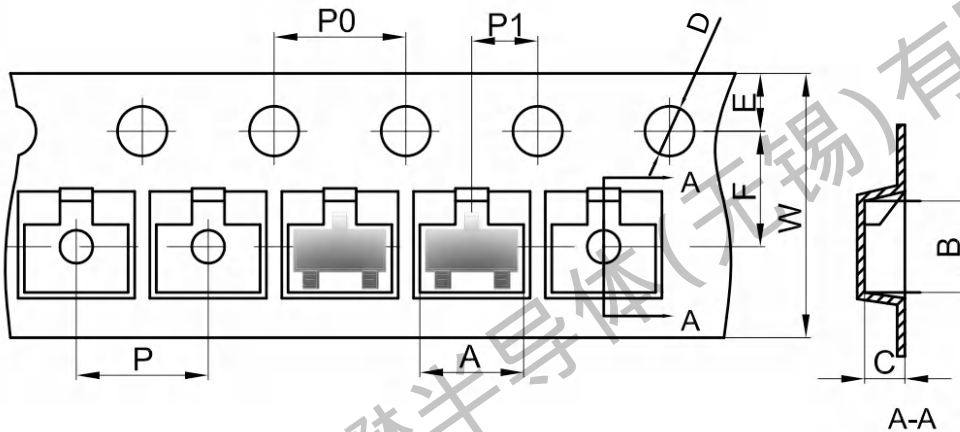
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SOT-23-3L Packing

1. The method of packaging and dimension are shown as below figure. (Dimension in mm)



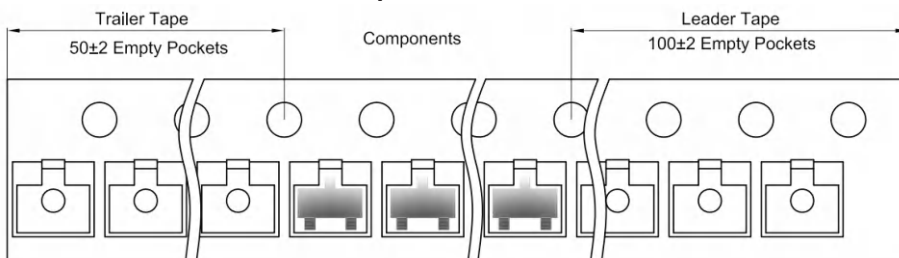
SOT-23-3L Embossed Carrier Tape



Dimensions are in millimeter

Pkg type	A	B	C	D	E	F	P0	P	P1	W
SOT-23-3L	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23-3L Tape Leader and Trailer



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Revision history:

Date	Rev	Description	Page
2023.08.06	23.08	Original	